

In the Specification

Please amend the paragraph beginning on page 3, line 31 as follows:

Embodiments of the present invention provide a capacitor having a dielectric structure having a first oxide layer having a first thickness, a layer of dielectric material on the first oxide layer and having a second thickness, the layer of dielectric material having a dielectric constant higher than the dielectric constant of the first oxide layer and a second oxide layer on the layer of dielectric material opposite the first oxide layer and having a third thickness. The first thickness is between about 0.5 and about 33 percent and the ~~second~~third thickness is between about 0.5 and about 33 percent of the sum of the first, second and third thicknesses.

Please amend the paragraph beginning on page 5, line 32 as follows:

In still further embodiments of the present invention, methods of fabricating capacitors as described above are provided by depositing a first oxide layer on a first metal layer so as to provide a first oxide layer having a first thickness, depositing a layer of dielectric material on the first oxide layer to provide a high dielectric layer having a second thickness, the layer of dielectric material having a dielectric constant higher than the dielectric constant of the first oxide layer and depositing a second oxide layer on the layer of dielectric material opposite the first oxide layer to provide a second oxide layer having a third thickness. The first thickness may be between about 0.5 and about 33 percent and the ~~second~~third thickness may be between about 0.5 and about 33 percent of the sum of the first, second and third thicknesses.